

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSVI)

2SK3568

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS(ON)} = 0.4 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 8.5S$ (typ.)
- Low leakage current: $I_{DSS} = 100 \mu A$ ($V_{DS} = 500 V$)
- Enhancement mode: $V_{th} = 2.0 \sim 4.0 V$ ($V_{DS} = 10 V, I_D = 1 mA$)

Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	500	V
Drain-gate voltage ($R_{GS} = 20 k\Omega$)		V_{DGR}	500	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	12	A
	Pulse ($t = 1 ms$) (Note 1)	I_{DP}	48	
Drain power dissipation ($T_c = 25^\circ C$)		P_D	40	W
Single pulse avalanche energy (Note 2)		E_{AS}	364	mJ
Avalanche current		I_{AR}	12	A
Repetitive avalanche energy (Note 3)		E_{AR}	4	mJ
Channel temperature		T_{ch}	150	$^\circ C$
Storage temperature range		T_{stg}	-55~150	$^\circ C$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	3.125	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

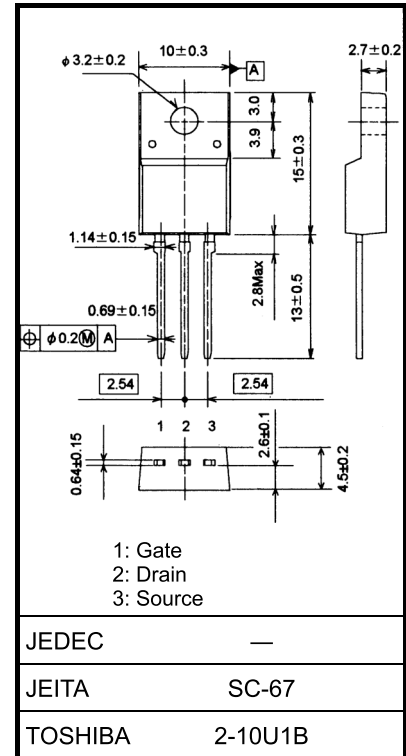
Note 1: Ensure that the channel temperature does not exceed $150^\circ C$.

Note 2: $V_{DD} = 90 V, T_{ch} = 25^\circ C$ (initial), $L = 4.3 mH, I_{AR} = 12 A, R_G = 25 \Omega$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.

Unit: mm



Weight : 1.7 g (typ.)

